## **REMARKS**

The purpose of this preliminary amendment is to clarify the translation of the application and to remove multiple dependent claims. Favorable consideration of this preliminary amendment is respectfully requested. If the Examiner believes that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at (248) 641-1600.

Respectfully submitted,

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## **ATTACHMENT FOR CLAIM AMENDMENTS**

The following is a marked up version of each amended claim in which underlines indicates insertions and brackets indicate deletions.

- 3. (Amended) A semiconductor device according to claim 1 [or claim 2] characterized in operating in a fully depleted operation mode.
- 4. (Amended) A semiconductor device according to [any one of] claim 1 [through claim 3], wherein the SOI substrate is a substrate composed of a glass substrate, a quartz substrate or another insulation substrate and a semiconductor film formed thereon.
- 8. (Amended) A method for manufacturing a semiconductor device according [any one of] claim 5 [through claim 7], wherein the junction depth of the extension regions is formed to be 50% or less of the junction depth of each of the source region and the drain region.